

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	623	257/532.ccls.	USPAT	OR	OFF	2005/03/31 11:38
S2	1428	silicidation	USPAT	OR	OFF	2002/08/06 21:27
S3	6	silicidation and inductor\$1	USPAT	OR	OFF	2003/07/25 01:56
S4	2	silicide adj prevention	USPAT	OR	OFF	2002/08/07 15:00
S5	209	257/531.ccls.	USPAT	OR	OFF	2003/11/29 19:40
S6	31	257/531.ccls. and doped near3 substrate	USPAT	OR	OFF	2002/08/07 15:15
S7	209	257/531.ccls.	USPAT	OR	OFF	2002/08/07 16:50
S8	623	257/532.ccls.	USPAT	OR	OFF	2002/08/07 16:50
S9	111	257/534.ccls.	USPAT	OR	OFF	2003/11/29 19:40
S10	114	257/535.ccls.	USPAT	OR	OFF	2003/11/29 19:40
S11	123	257/621.ccls.	USPAT	OR	OFF	2002/08/07 16:51
S12	0	257/531.ccls. and 257/532.ccls. and 257/534.ccls. and 257/535.ccls. and 257/621.ccls.	USPAT	OR	OFF	2002/08/07 16:51
S13	1035	257/531.ccls. or 257/532.ccls. or 257/534.ccls. or 257/535.ccls. or 257/621.ccls.	USPAT	OR	OFF	2002/08/07 16:52
S14	33	(257/531.ccls. or 257/532.ccls. or 257/534.ccls. or 257/535.ccls. or 257/621.ccls.) and doped adj substrate	USPAT	OR	OFF	2005/03/31 09:16
S15	40	inductor and (doped adj substrate)	USPAT	OR	OFF	2002/08/07 17:19
S16	410	(silicidation or silicide) and inductor\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/31 12:21
S17	261	257/531.ccls.	USPAT	OR	OFF	2005/03/31 09:16
S18	1489	257/532.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/07/25 02:44
S19	442	257/531.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/07/25 02:44
S20	237	257/534.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/07/25 02:44

S21	153	257/535.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/07/25 02:44
S22	333	257/621.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/07/25 02:44
S23	3305	(silicidation or silicide or sin or (silicon near3 nitride)) and (inductor\$1 or (spiral near3 conductor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/29 19:20
S24	353	(silicidation or silicide or sin or (silicon near3 nitride)) SAME (inductor\$1 or (spiral near3 conductor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/29 20:09
S25	1547	257/532.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/29 19:40
S26	486	257/531.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/29 21:08
S27	243	257/534.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/29 19:40
S28	165	257/535.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/29 19:40
S29	346	257/621.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/29 19:41
S30	2543	257/532.ccls. or 257/531.ccls. or 257/534.ccls. or 257/535.ccls. or 257/621.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/29 19:41

S31	377	(257/532.ccls. or 257/531.ccls. or 257/534.ccls. or 257/535.ccls. or 257/621.ccls.) and (inductor or (spiral near3 conductor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/29 19:42
S32	328	((257/532.ccls. or 257/531.ccls. or 257/534.ccls. or 257/535.ccls. or 257/621.ccls.) and (inductor or (spiral near3 conductor))) not ((silicidation or silicide or sin or (silicon near3 nitride)) SAME (inductor\$1 or (spiral near3 conductor)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/29 19:42
S33	5	(protrution or protruding near5 substrate) SAME (inductor\$1 or (spiral near3 conductor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/29 20:10
S34	5	((protrution or protruding) near5 substrate) SAME (inductor\$1 or (spiral near3 conductor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/29 20:10
S35	315	257/528.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/29 21:16
S36	113	438/329.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/31 10:43
S37	1	("6730983").PN.	USPAT	OR	OFF	2005/03/18 19:38
S38	608	257/531.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/31 10:39
S39	286	257/534.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/31 10:39
S40	201	257/535.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/31 09:39

S41	394	257/621.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/31 09:37
S42	44	(257/531.ccls. or 257/532.ccls. or 257/534.ccls. or 257/535.ccls. or 257/621.ccls.) and doped adj substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/31 09:37
S43	136	438/329.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/31 13:44
S44	1789	257/532.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/31 11:51
S45	423	257/528.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/31 12:11
S48	1594	257/700.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/31 12:12
S50	1261	257/701.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/31 12:12
S51	2678	S48 S50	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/31 12:12

S52	91	S51 and (inductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/31 12:13
S54	661	(silicidation or silicide) and inductor\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/31 12:21
S55	551	438/381.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/31 13:44
S56	533	S55 not S54	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/31 13:44
S57	514	S56 not S43	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/31 13:44
S58	2649	S41 S42 S43 S44 S45 S52	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/31 13:45
S59	480	S57 not S58	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/31 13:45